

Fundamental Microscopic Studies on the Etching Behavior of Silver Pastes on Poly-Si/SiO_x Passivating Contacts



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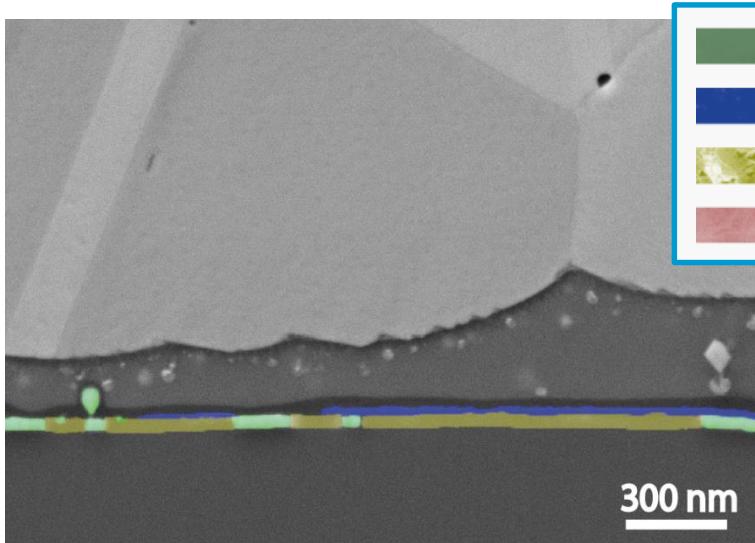
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MiW2023, Neuchâtel – May 8th, 2023

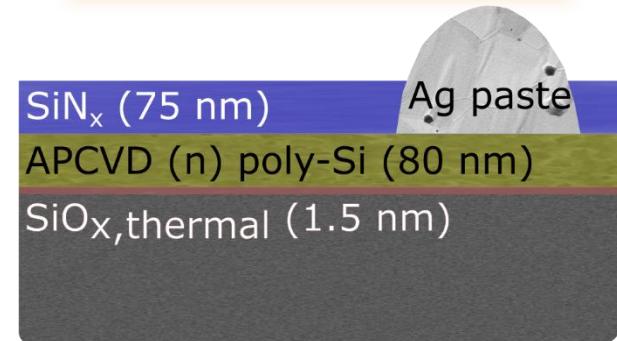
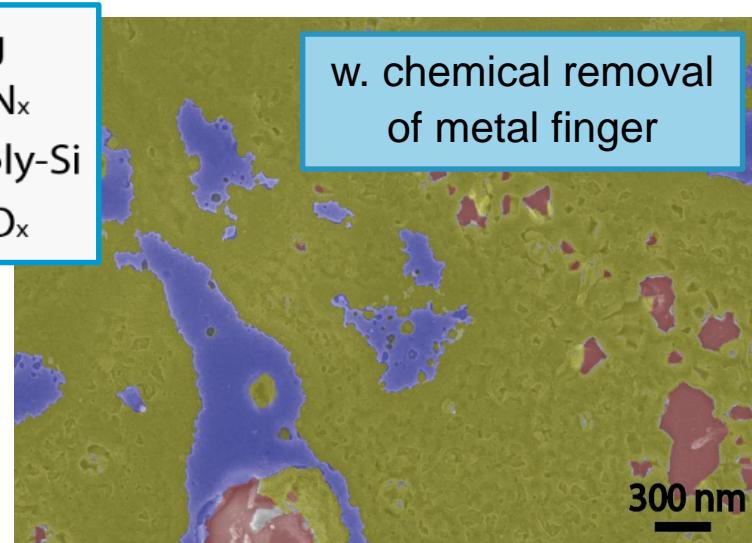
Etching of Ag Paste in Poly-Si/SiO_x Contacts

~1 s
 T_{meas} 814°C
Air, BF

Cross section

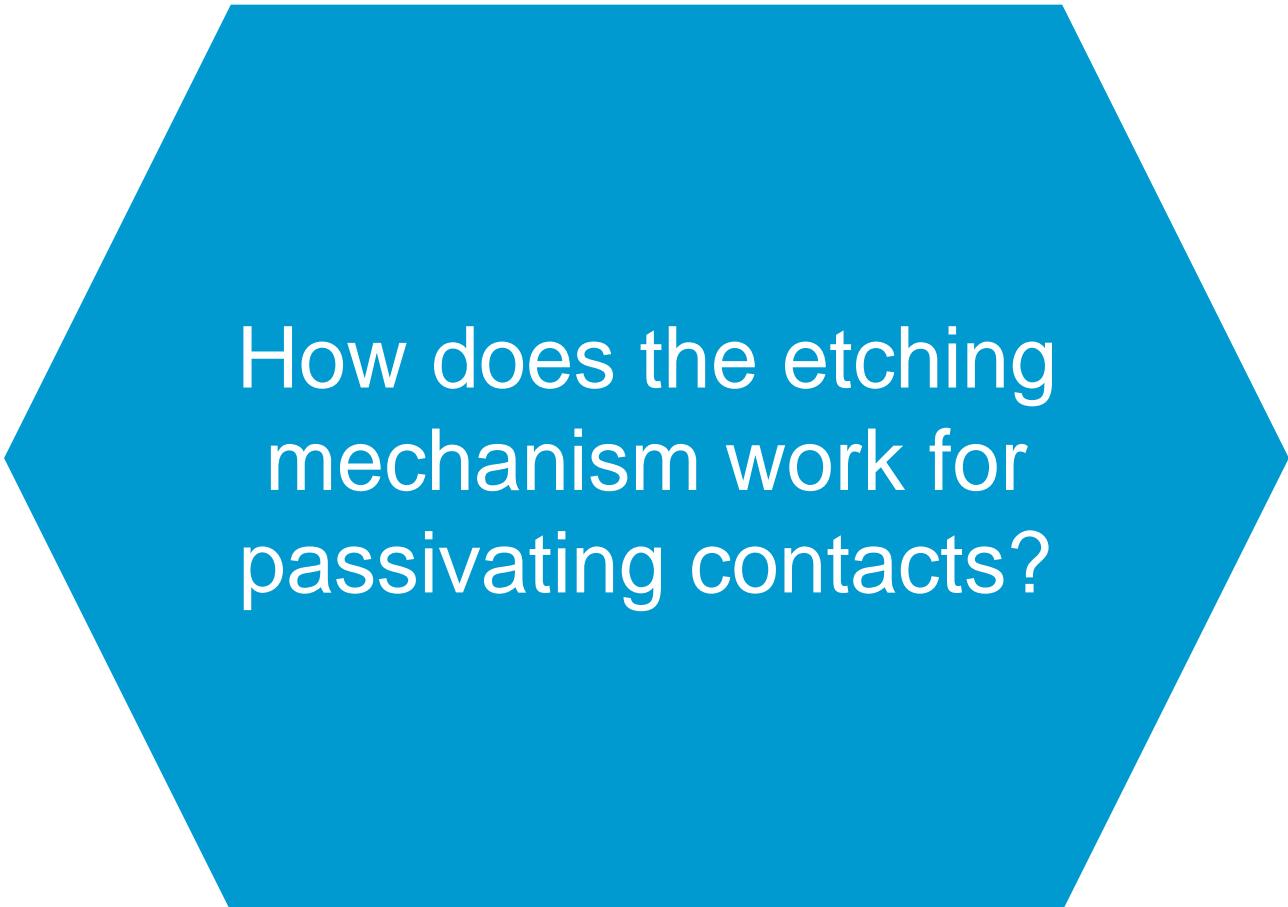


Top view



- Etching results in Ag crystallites in poly-Si layer
- No penetration of c-Si substrate by Ag crystallites (planar samples)
- Ag crystallites remove nearly total poly-Si layer

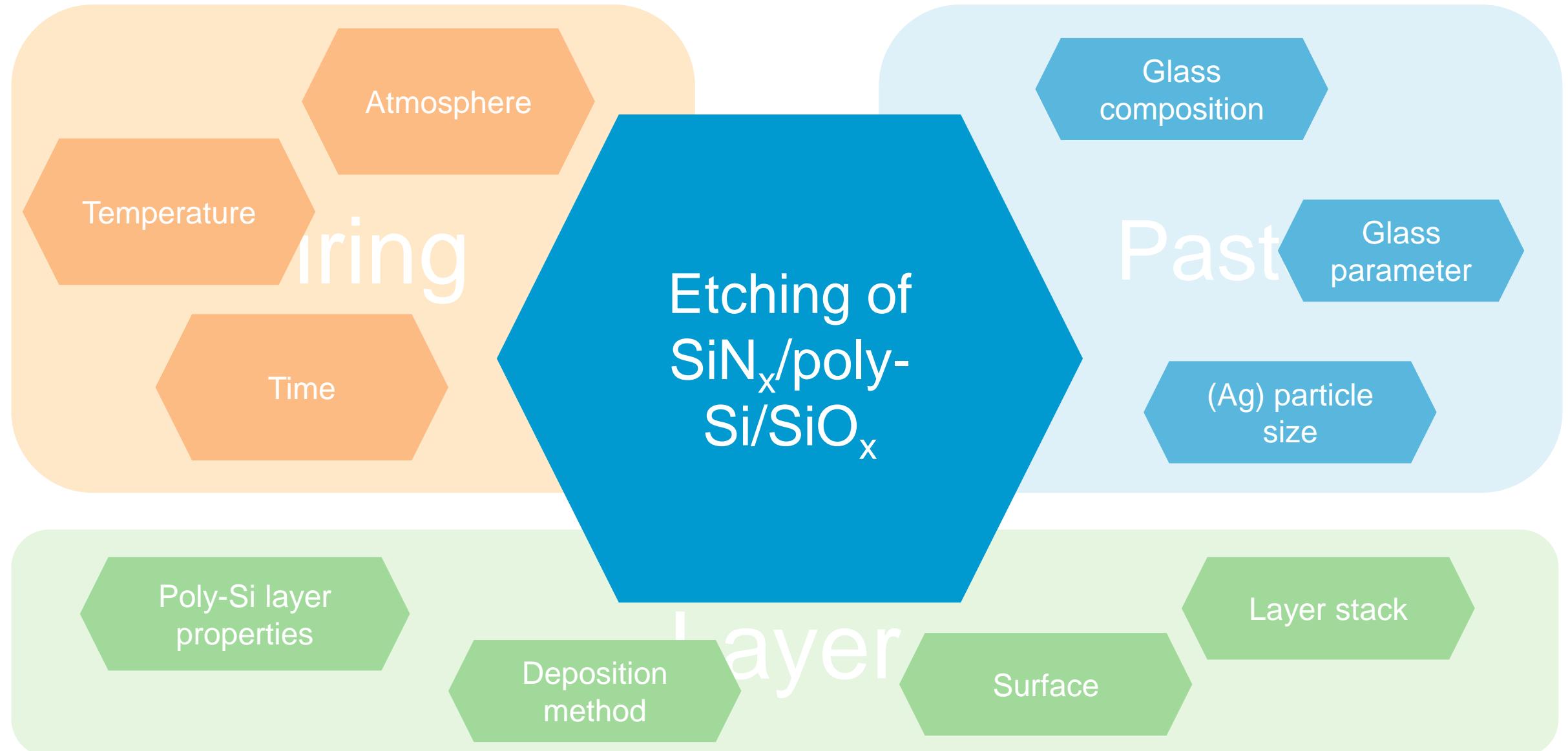
Discussed in Glatthaar et al. Phys.
Status Solidi A **219**, 2200501 (2022).



How does the etching
mechanism work for
passivating contacts?

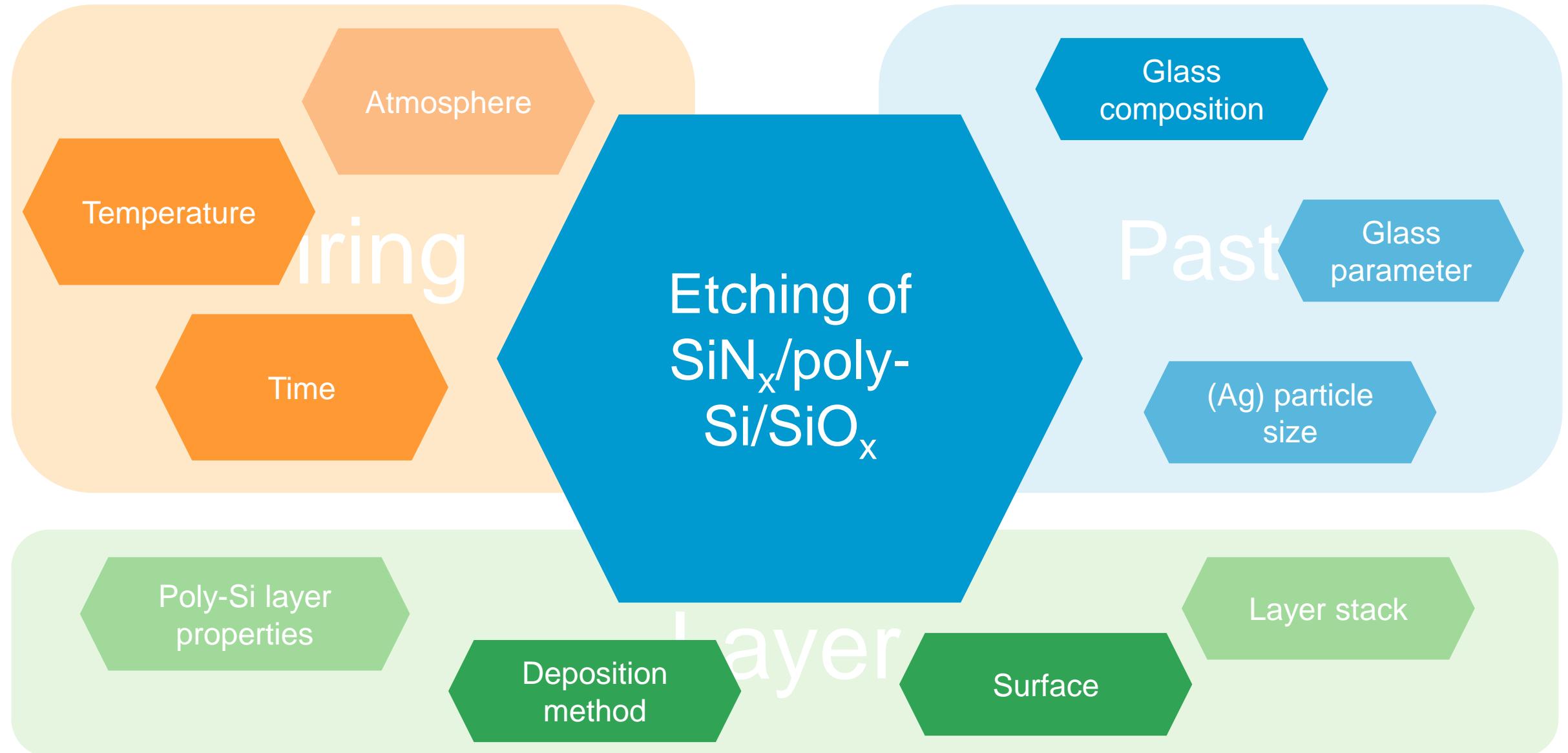
Impact on Ag Paste Etching Mechanism

No complete overview



Impact on Ag Paste Etching Mechanism

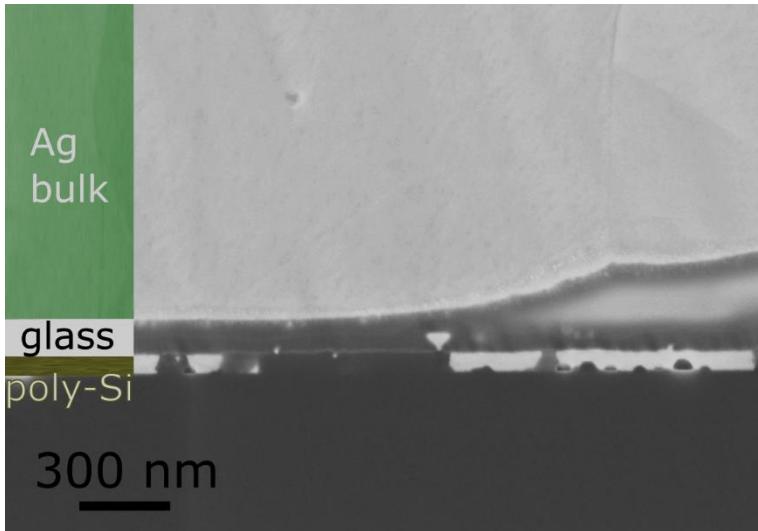
No complete overview



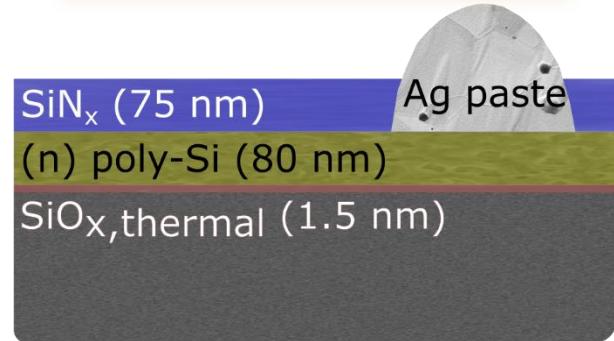
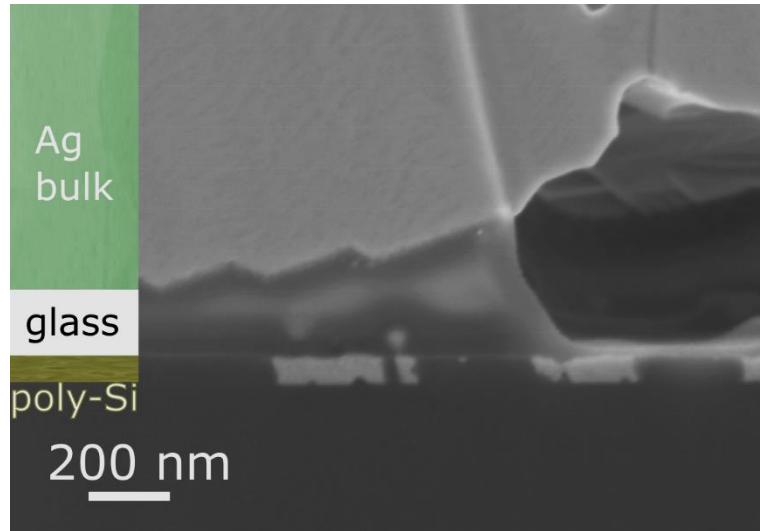
Poly-Si Layer from Different Deposition Methods

T_{meas} 814°C
N₂, RTP

APCVD



PECVD



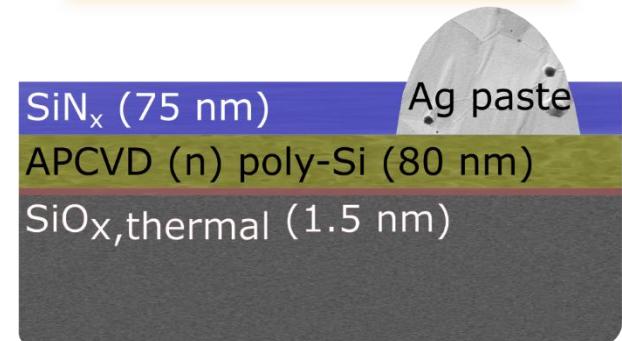
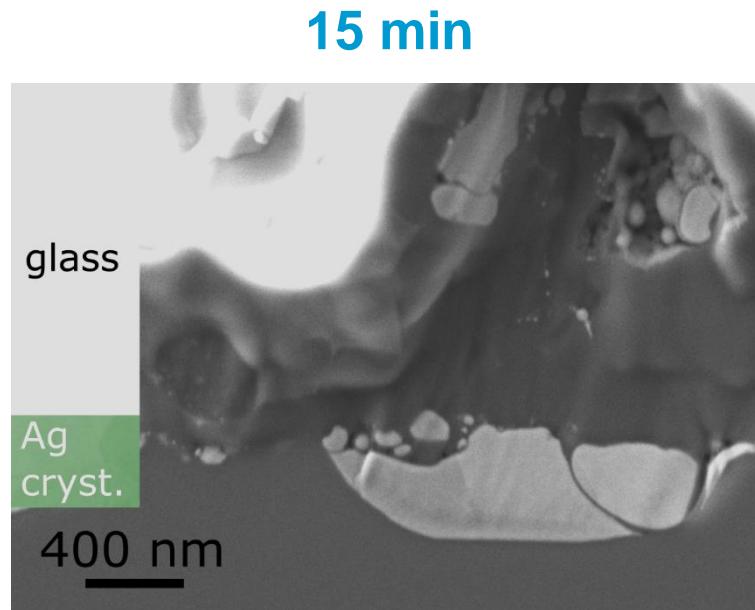
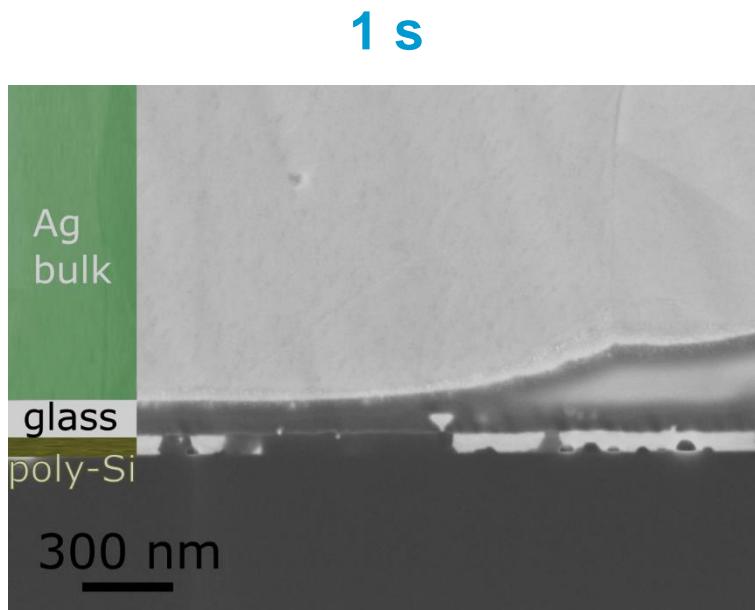
- Ag crystallite formation comparable between APCVD and PECVD
 - No statistically significant differences in glass layer thickness and Ag crystallite density
 - ρ_C with $<1 \text{ m}\Omega\text{cm}^2$ slightly lower for PECVD samples (data not shown here)



Process Time Variation

1 s &
15 min

T_{meas} 829°C
 N_2 , RTP



- Poly-Si layer completely dissolved after 15 min
- Massive etching into c-Si substrate
- Formation of up to 500 nm Ag crystallites and thick glass layer

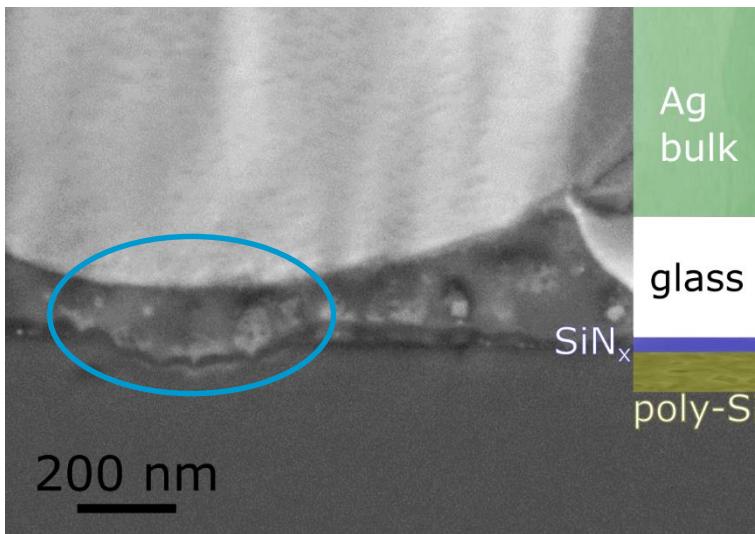


Temperature and Process Time Variation

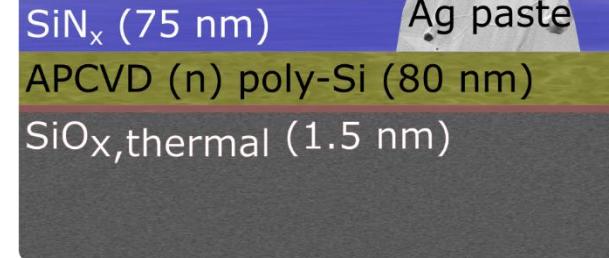
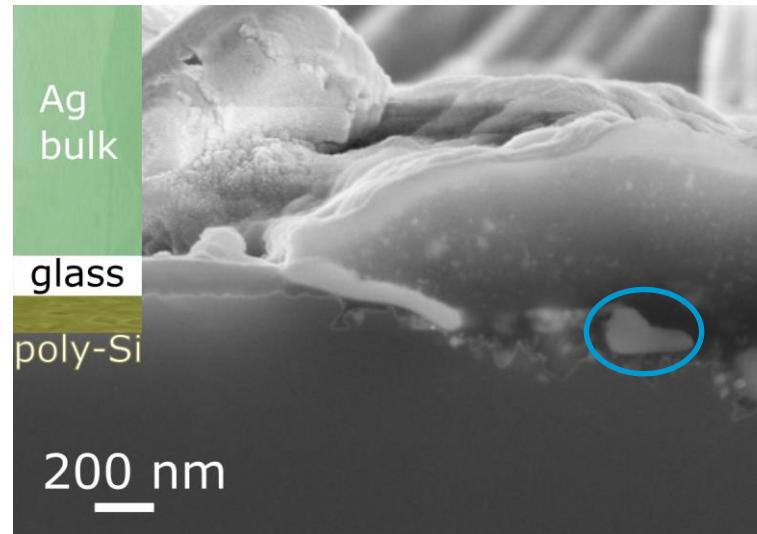
1 min &
15 min

T_{meas} 606°C
 N_2 , RTP

1 min



15 min



- Slight and non-selective etching into poly-Si layer
- No Ag crystallite formation in poly-Si layer after 1 min
- Strong etching into c-Si substrate after 15 min
- Some Ag crystallites/phases visible after 15 min (detected by EDX)



Impact of Glass Frit Composition

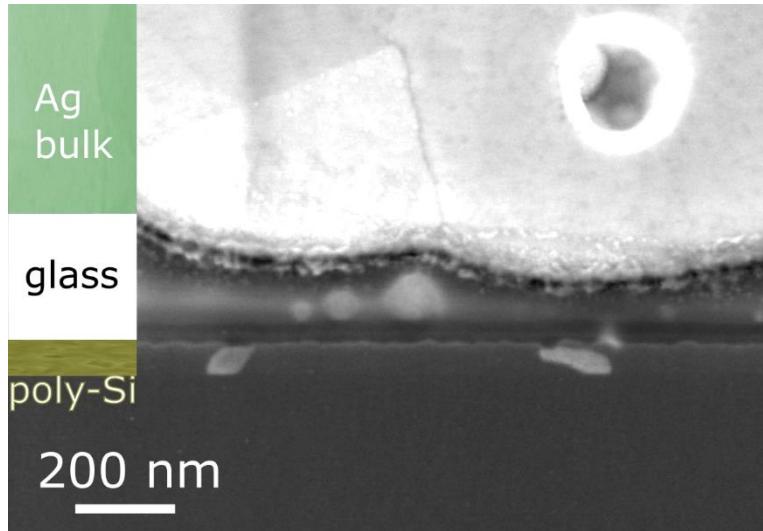
Paste variations:

- Industrial paste formulation with
 - Pb based glass frit
 - Te based glass frit
- Experimental paste without glass frit

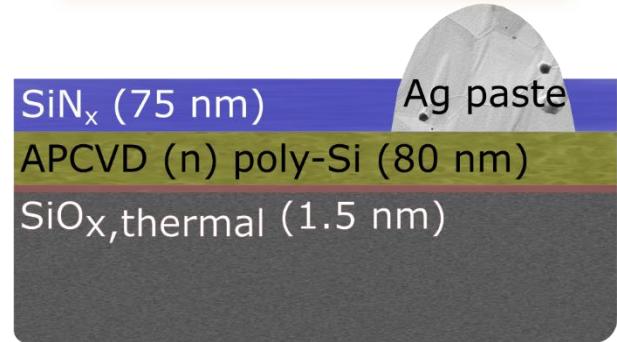
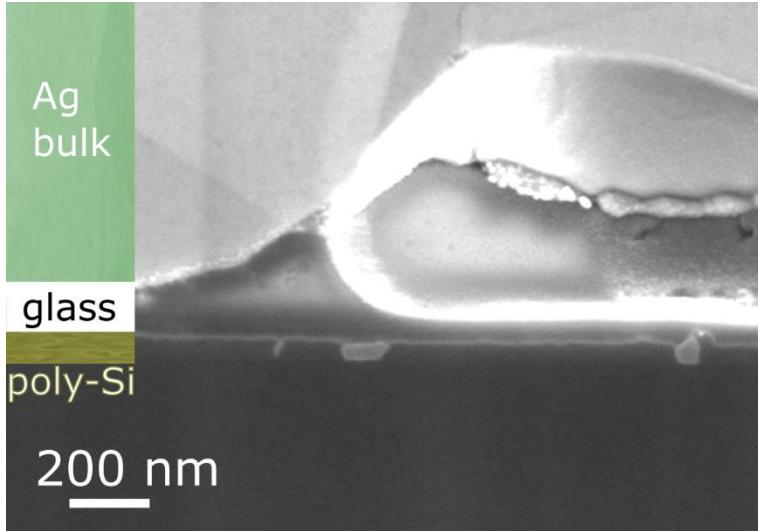
Impact of Main Component of Glass Frit



Te based



Pb based



- Ag crystallite formation in poly-Si layer
- No statistically significant differences in glass layer thickness and Ag crystallite density

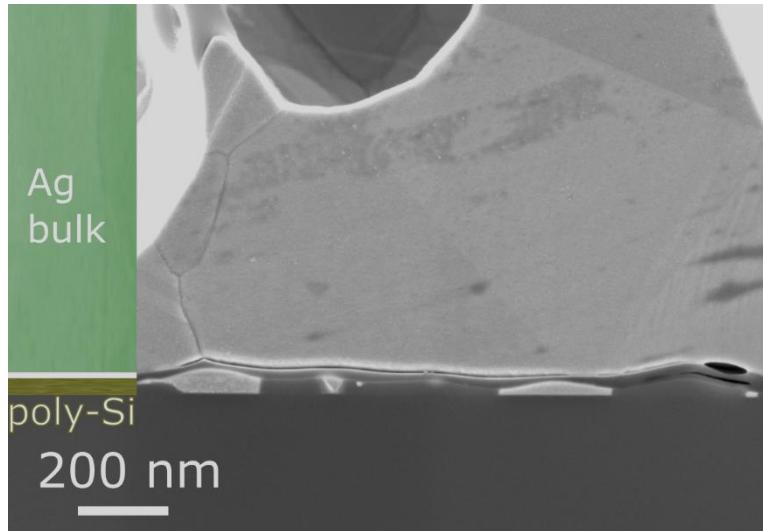


Ag Paste without Glass Frit

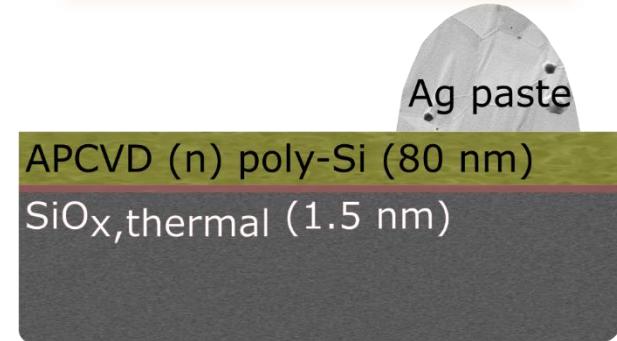
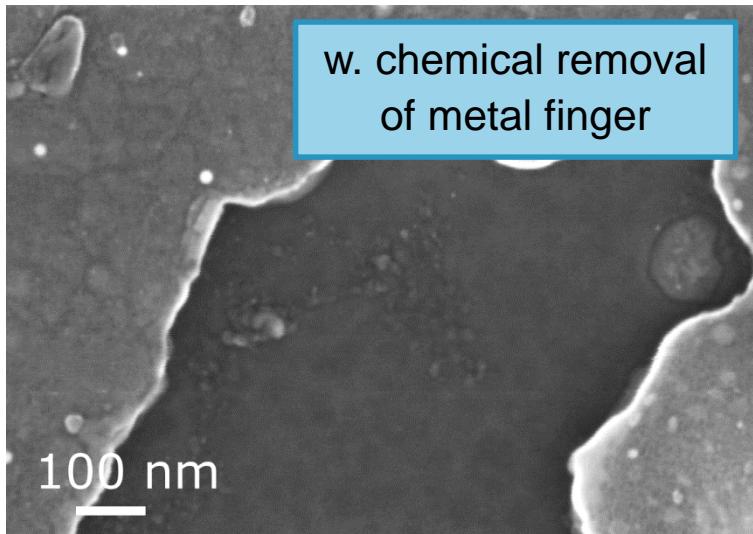
15 min

T_{actual} 829°C
Ar, RTP

Cross section



Top view



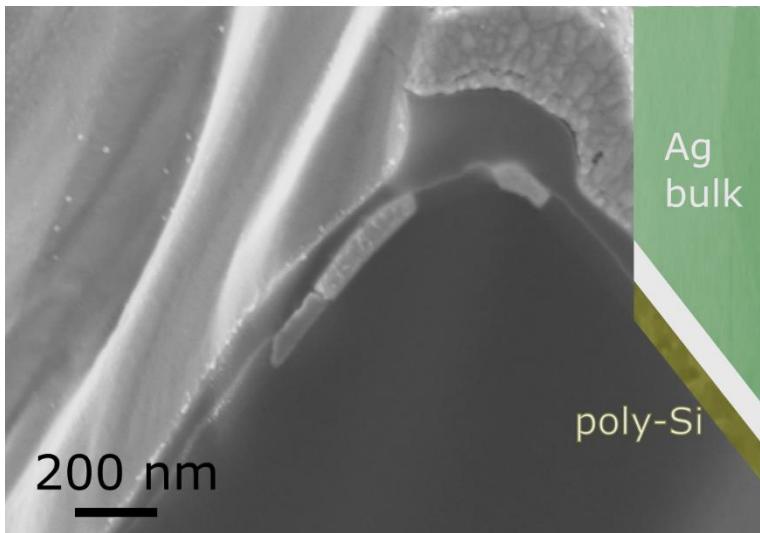
- Ag crystallite formation in poly-Si layer
- No etching into c-Si substrate visible
- Unclear why poly-Si layer is etched inhomogeneously
- Poly-Si identified by phosphorous peak in EDX



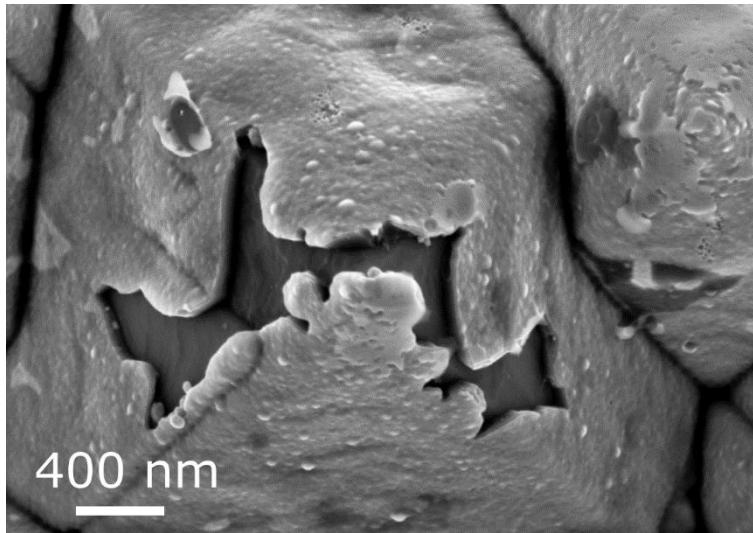
Ag Paste without Glass Frit

15 min
 $T_{\text{actual}} 829^{\circ}\text{C}$
Ar, RTP

Cross section



Top view



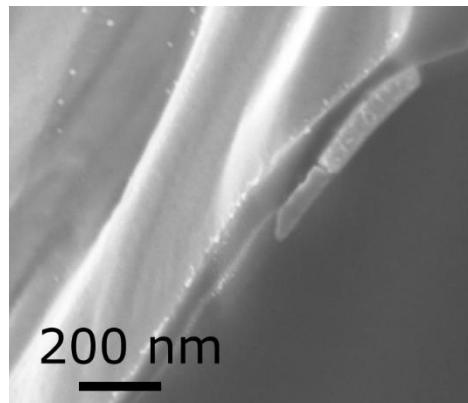
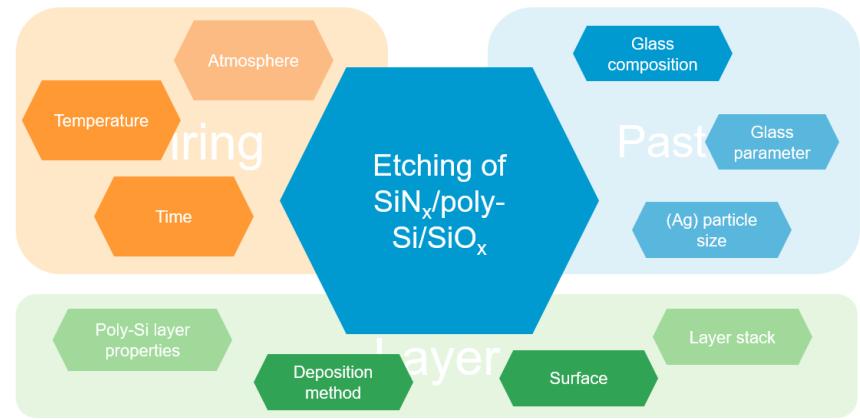
- Ag crystallite formation in poly-Si layer
- No etching into c-Si substrate visible
- Contrast to samples with glass frit

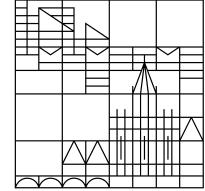
Glatthaar et al. Phys. Status Solidi A **219**, 2200501 (2022).



Summary

- Multiple parameters influence crystallite formation
- APCVD or PECVD and Pb or Te based glass frit differ not significantly in contact formation
- Process temperature and time strongly influence etching behavior
- Etching of poly-Si layer by Ag^+ without glass frit possible





Thank you for your attention!

Questions!

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This work was partially funded by the German Federal Ministry for Economic Affairs and Climate Action contract number 03EE1022C (project FUN) and by the Netherlands under the Dutch contract no. SOL18004 both within solar-era net.